

**CMPD2836
CMPD2838**

**DUAL SILICON
SWITCHING DIODE**



SOT-23 CASE

**Central™
Semiconductor Corp.**

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD2836, CMPD2838 types are ultra-high speed silicon switching diodes manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

The following configurations are available:

CMPD2836 DUAL, COMMON ANODE
CMPD2838 DUAL, COMMON CATHODE

MARKING CODE: CA2
MARKING CODE: CA6

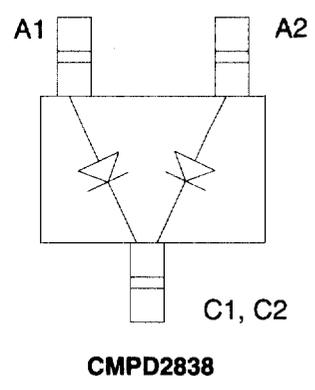
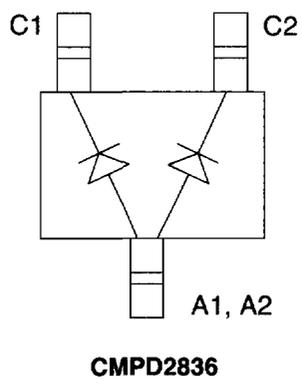
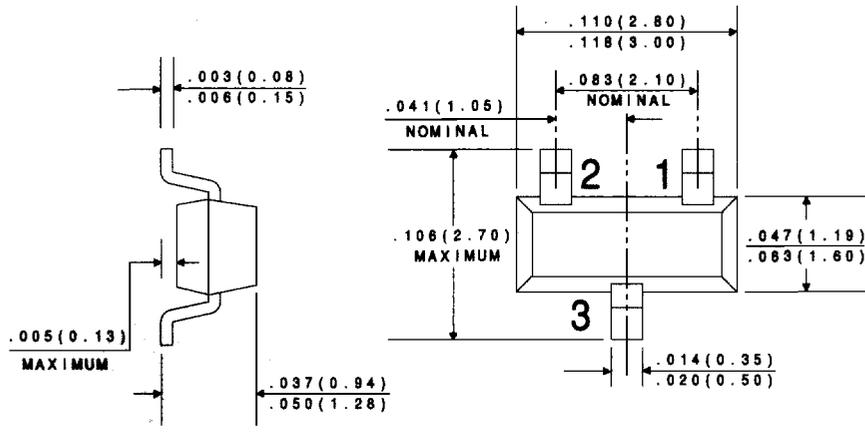
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	75	V
Average Forward Current	I_O	200	mA
Peak Forward Current	I_{FM}	300	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	357	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV_R	$I_R=100\mu\text{A}$	75			V
I_R	$V_R=50\text{V}$			100	nA
V_F	$I_F=10\text{mA}$			1.0	V
V_F	$I_F=50\text{mA}$			1.0	V
V_F	$I_F=100\text{mA}$			1.2	V
C_T	$V_R=0, f=1\text{ MHz}$		1.5	4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$			4.0	ns

All dimension in inches (mm).



DATA SHEET

R2